

Diopside

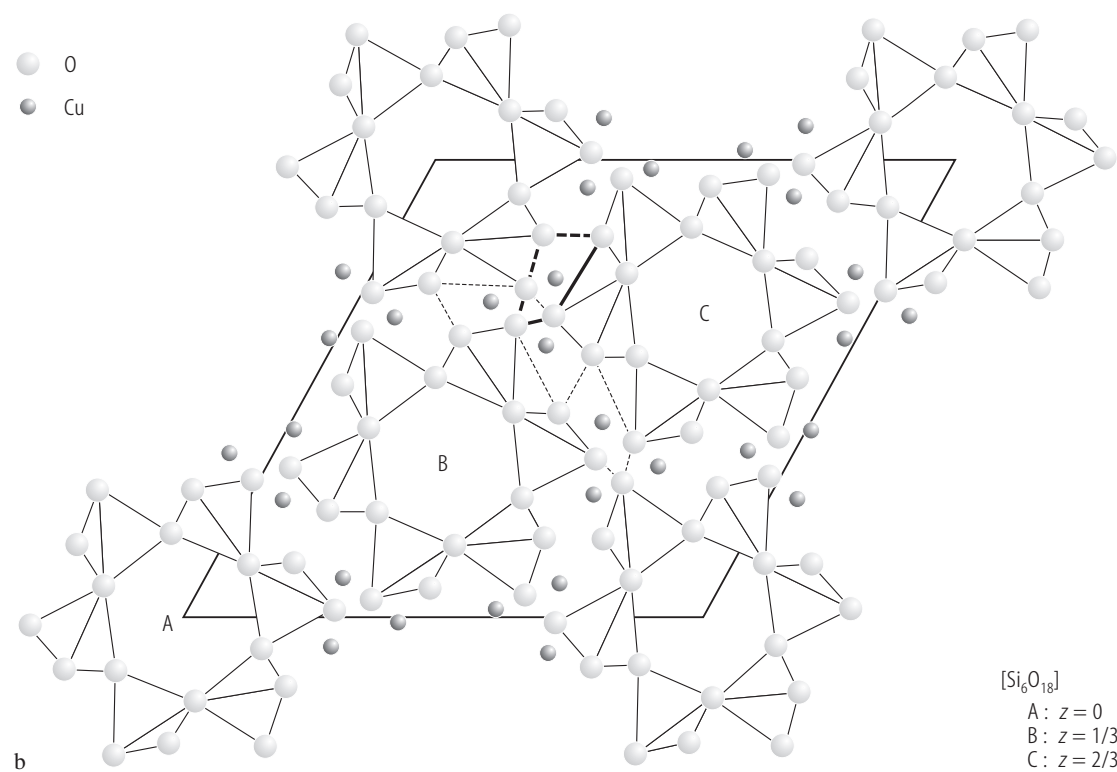
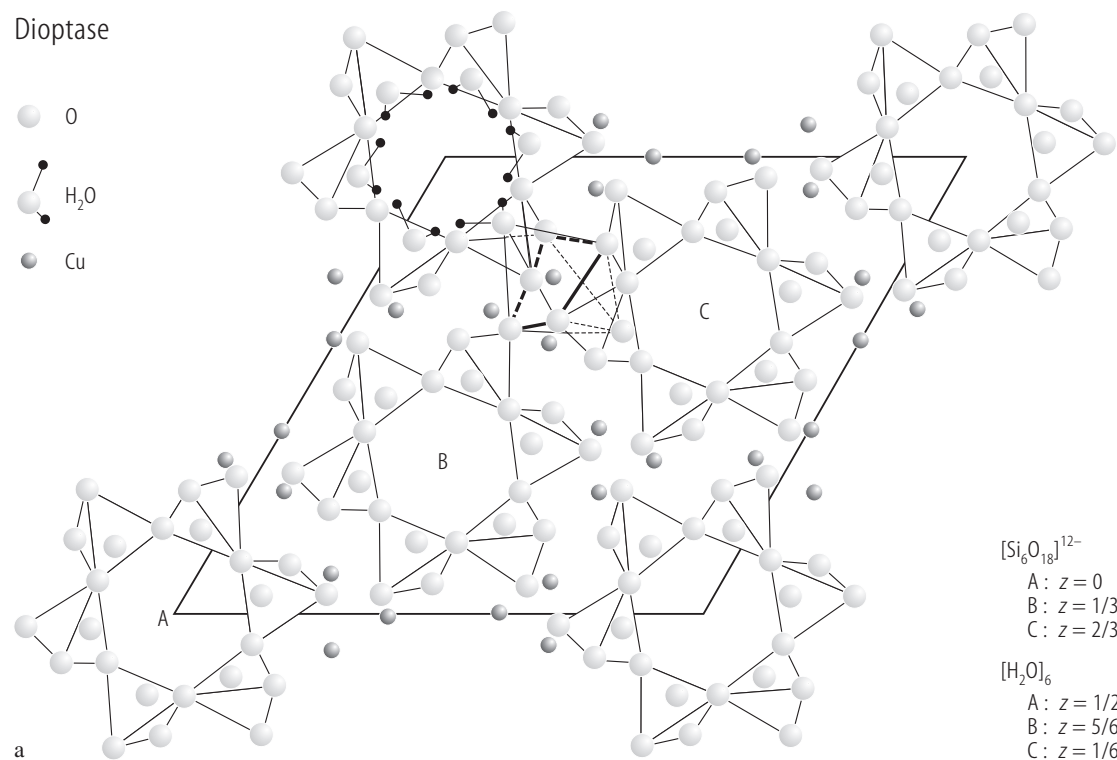


Fig. 1. Diopside. Crystal structures: (a) green [77R1, 89B1]; (b) black [89B1].

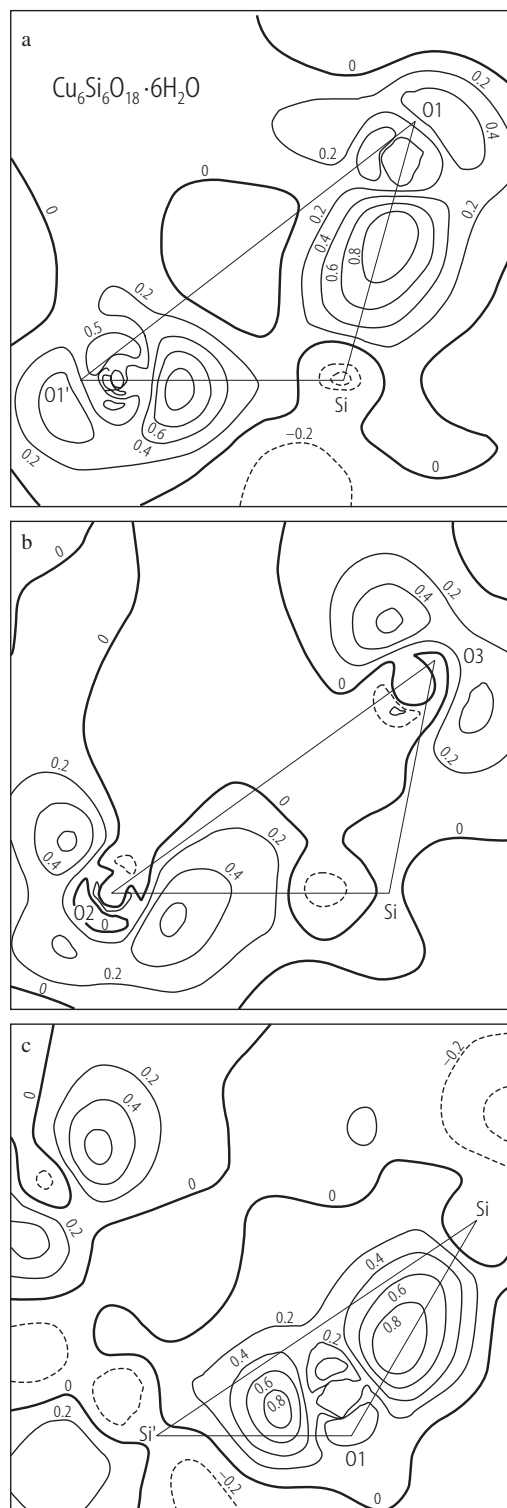


Fig. 2. $\text{Cu}_6\text{Si}_6\text{O}_{18} \cdot 6\text{H}_2\text{O}$. Static deformation density in SiO_4 tetrahedron sections: (a) O1-Si-O1'; (b) O2-Si-O3; (c) Si-O1-Si'. Contour interval is $0.2 \text{ e}\text{\AA}^{-3}$; zero level is given by bold, negative by dashed, and positive by solid lines [02B1].

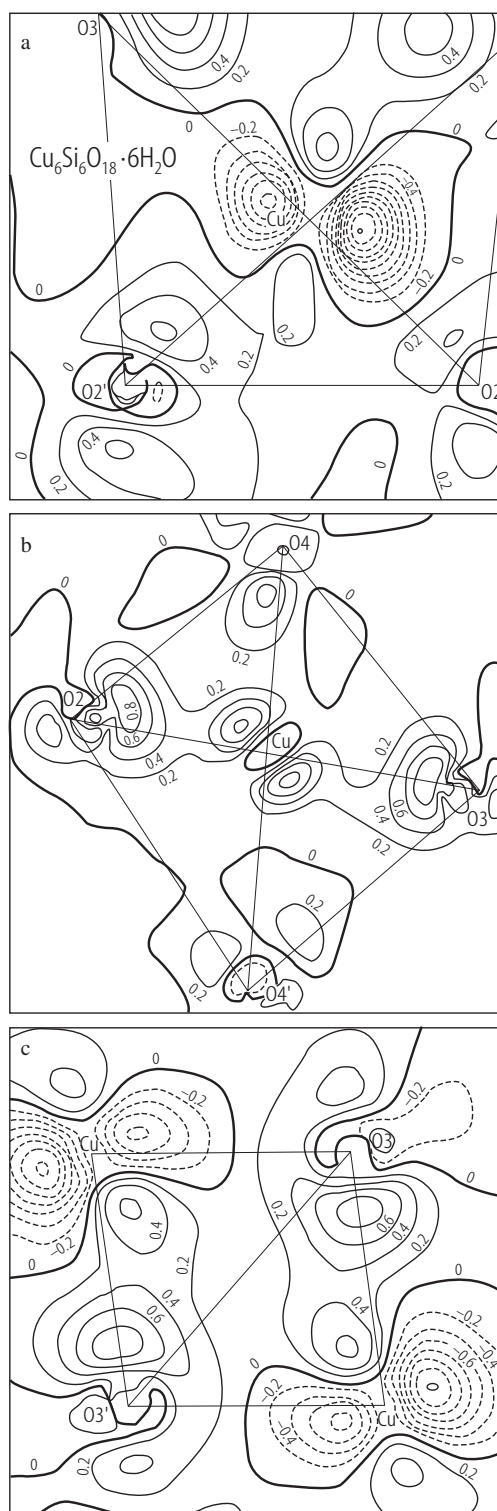


Fig. 3. $\text{Cu}_6\text{Si}_6\text{O}_{18} \cdot 6\text{H}_2\text{O}$. Static deformation density in Cu octahedron sections. (a) Via Cu, O2, O2', O3, O3'; (b) combined from four triangles via the apical water molecule O4, O4', O2, and O3; (c) via Cu-Cu' pairs with common edge O3, O3' [02B1].

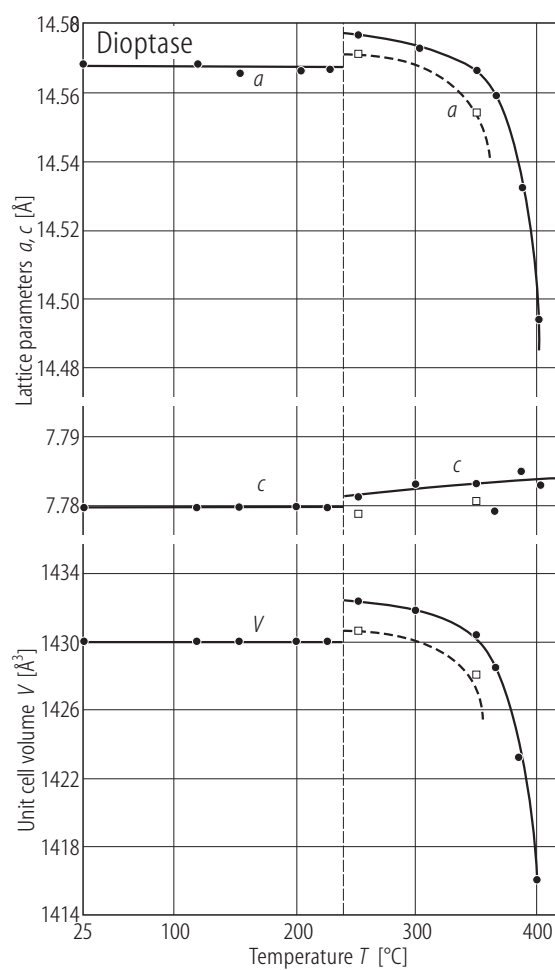


Fig. 4. Diopside. Lattice parameters of hydrothermally annealed and quenched samples. Silicates kept for 2 days (dots) and 16 days (squares) at 0.5 kbar at various temperatures [88B1].

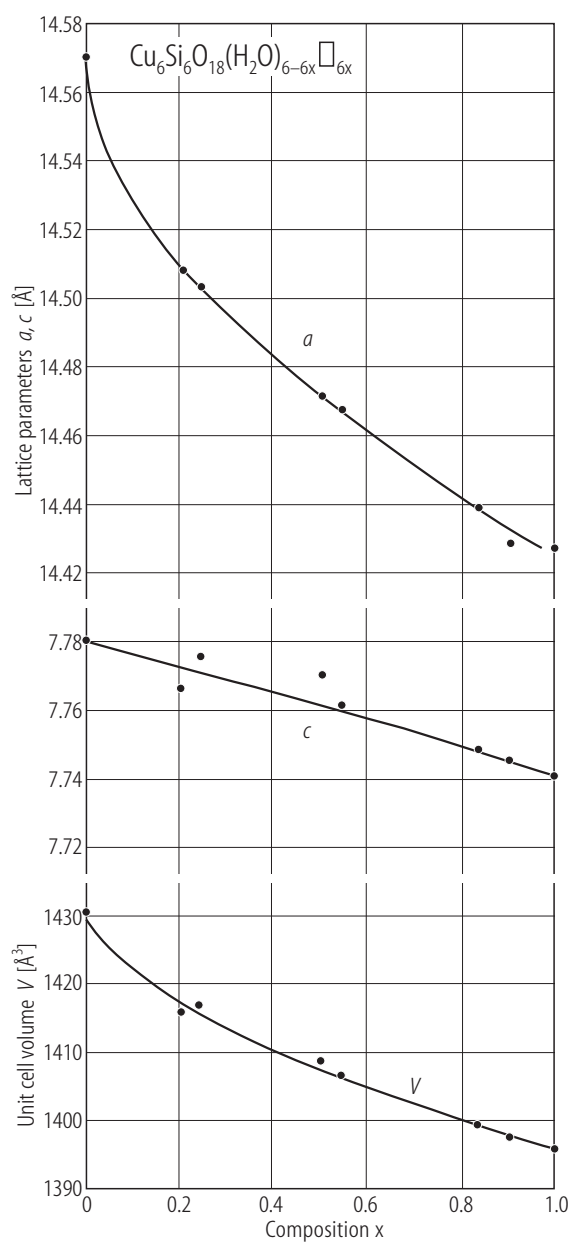


Fig. 5. $\text{Cu}_6\text{Si}_6\text{O}_{18}(\text{H}_2\text{O})_{6-6x}\square_{6x}$. Lattice parameters as function of x , after annealing at 600°C in air [88B1].

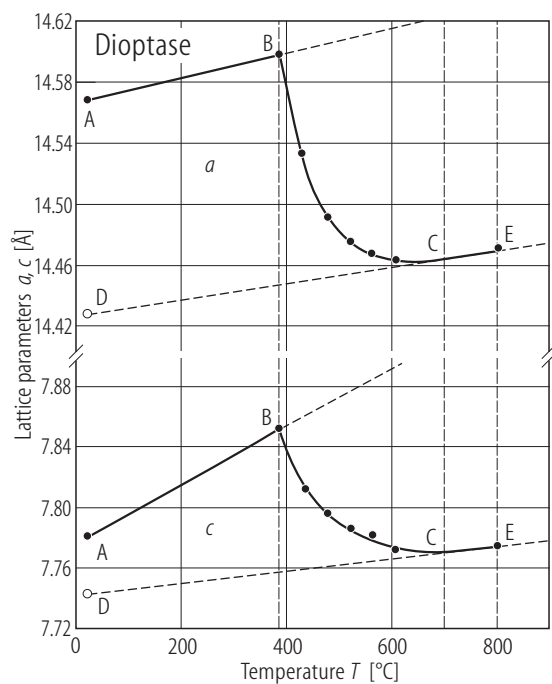


Fig. 6. Diopside. Lattice parameters from a continuous high-temperature pattern starting with green diopside ($0.3^\circ\text{C}/\text{min}$). Black diopside at room temperature A and D; B: begin of dehydration, C: end of dehydration; E: end of visible diopside reflections [88B1].

For Fig. 7 see next page

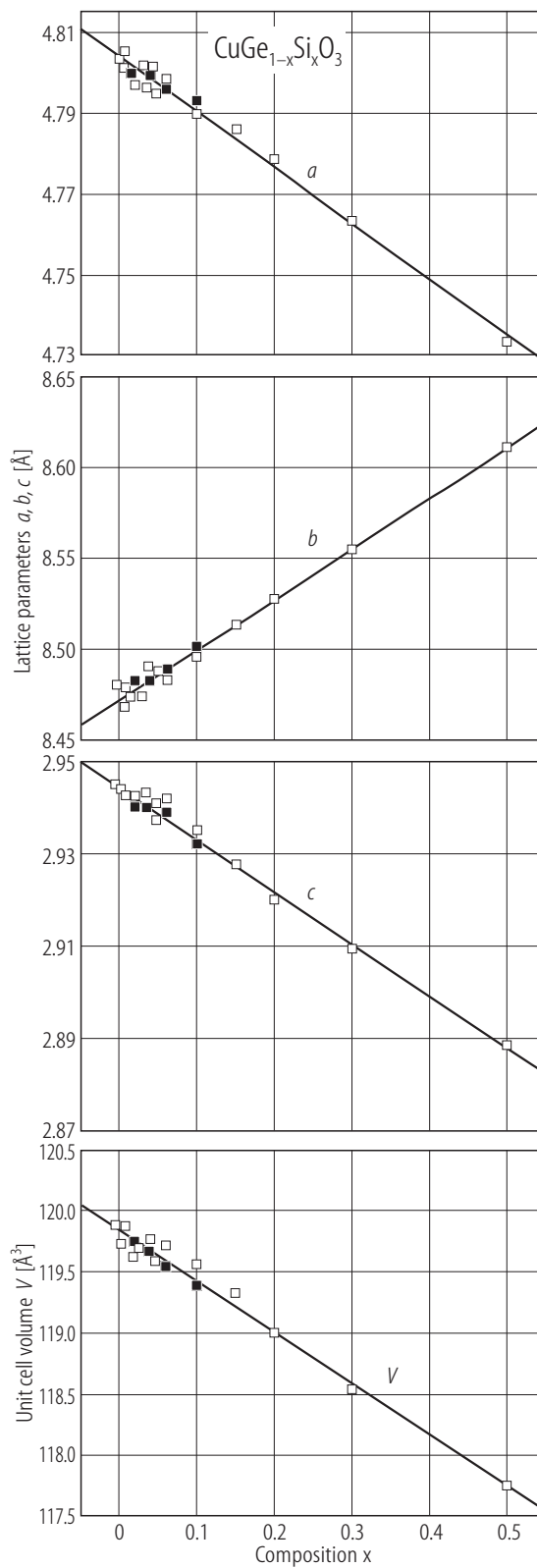


Fig. 8. $\text{CuGe}_{1-x}\text{Si}_x\text{O}_3$. Composition dependences of lattice parameters. The solid line represents a linear fit of the data. No difference between polycrystalline (\square) and single crystal (\blacksquare) samples was observed [97W1].

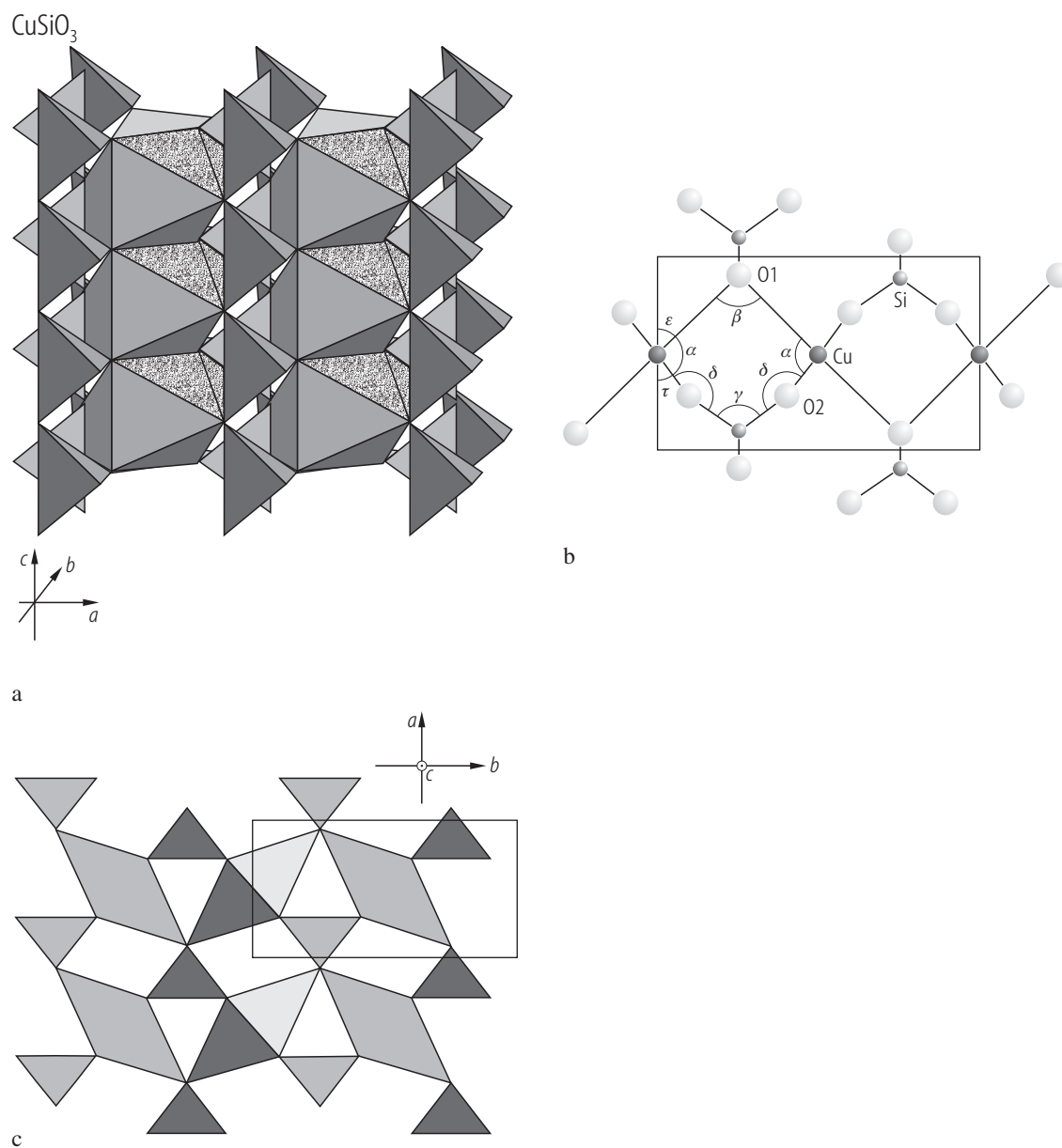


Fig. 7. CuSiO_3 . **(a)** Picture of the crystal structure showing the connection of silicate and cuprate chains running down the c -axis; **(b)** projection of the crystal structure along c [96B1, 98B1]; **(c)** polyhedra drawing of the crystal structure as projected down [001] showing the empty structural channels. The projected unit cell is outlined [04W1].

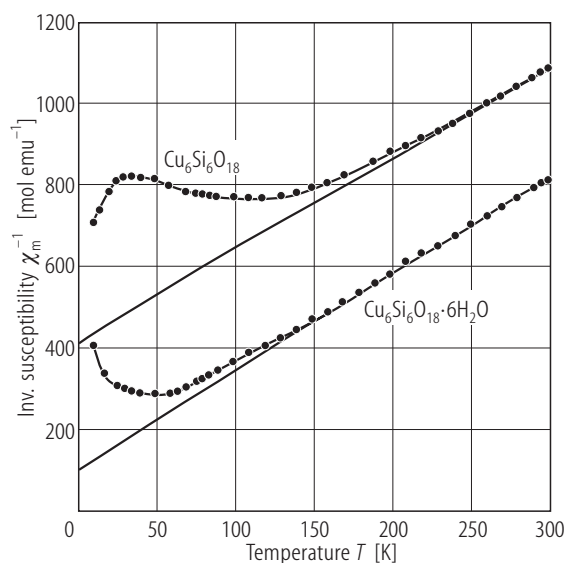
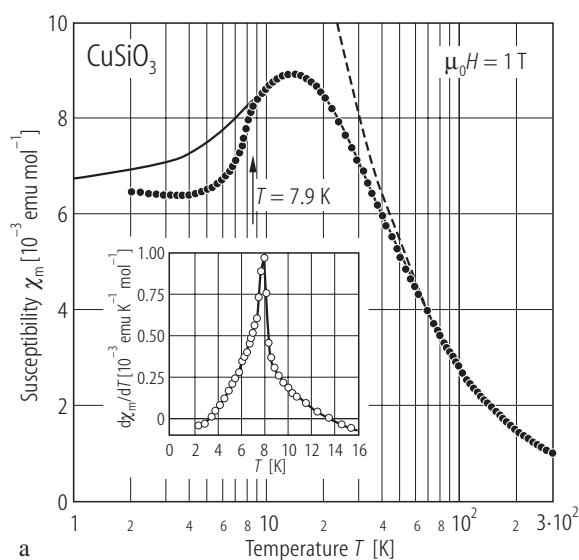
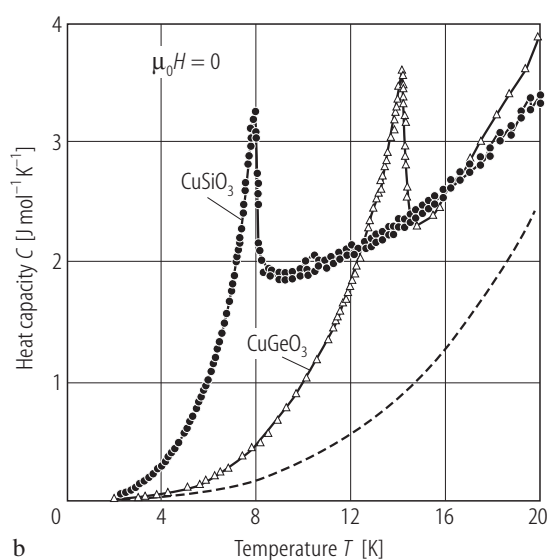


Fig. 9. $\text{Cu}_6\text{Si}_6\text{O}_{18}\cdot 6\text{H}_2\text{O}$ and $\text{Cu}_6\text{Si}_6\text{O}_{18}$. Thermal variations of inverse susceptibilities [93W1].

For Fig. 10 see next page



a



b

Fig. 11. CuSiO_3 . **(a)** Temperature dependence of the magnetic susceptibility in a log T scale [00B1]. The solid curve corresponds to the numerical calculations for $S = \frac{1}{2}$ 1D Heisenberg chains with nearest-neighbour coupling and without next-nearest neighbour coupling [98K1]. The fitting of the numerical results to the experimental $\chi_m(T)$ requires $J/k_B = 21$ K and an effective moment $p_{\text{eff}} = 1.60 \mu_B/\text{Cu}$

atom. At $T \geq 200$ K, $\chi_m(T)$ was fitted with a Curie-Weiss law (dashed line) with $p_{\text{eff}} = 1.56 \mu_B/\text{Cu atom}$ and $\Theta = -7.2$ K. The inset shows $d\chi_m/dT$ as function of temperature [00B1]. **(b)** Heat capacity of CuMO_3 for $M = \text{Ge}$ [95L1] and Si [00B1]. The dashed line represents the phonon contribution $C_{\text{ph}} = \beta T^3$ for CuGeO_3 with $\beta = 0.32 \text{ mJ/mol K}^4$.

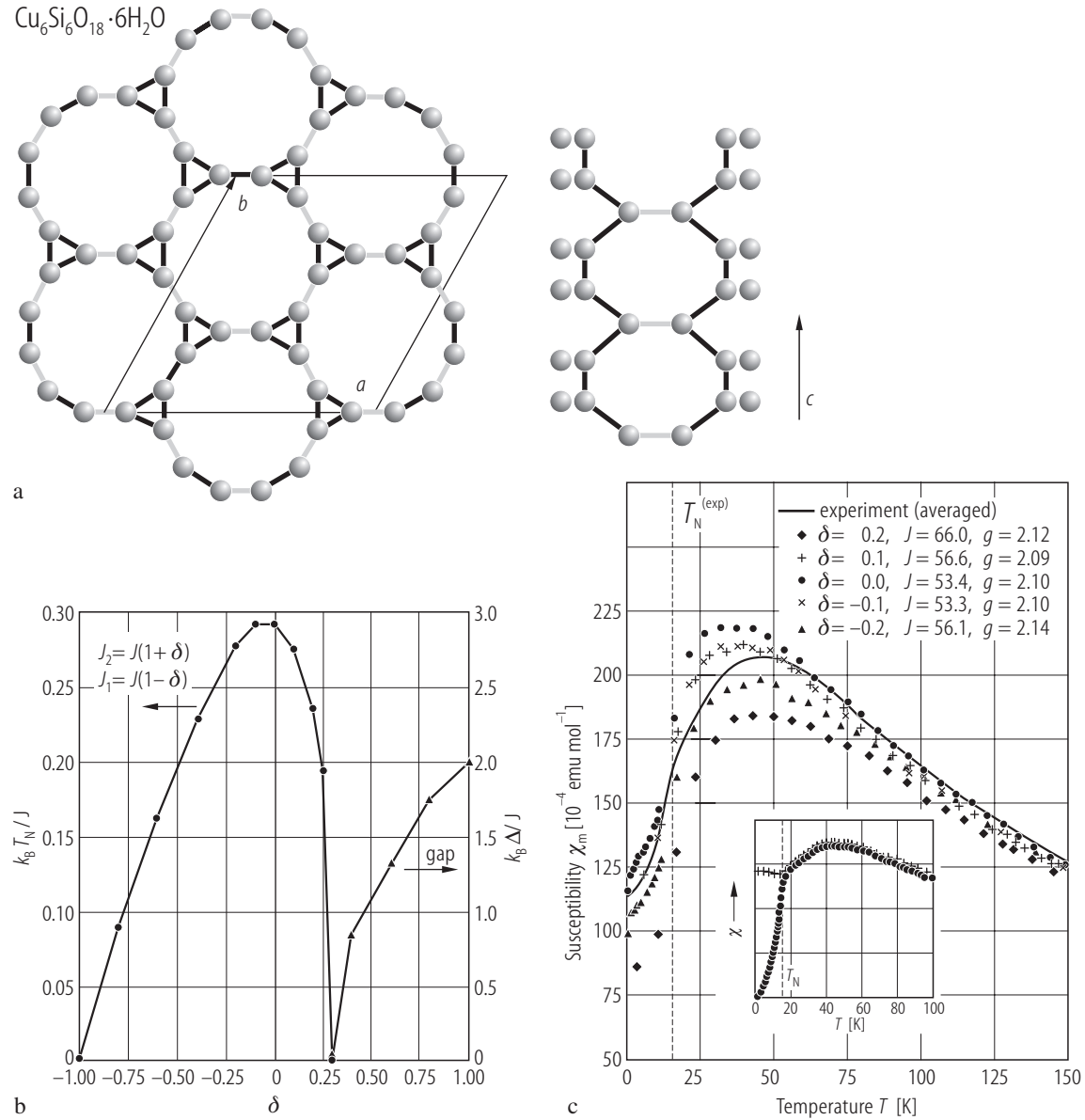


Fig. 10. $\text{Cu}_6\text{Si}_6\text{O}_{18} \cdot 6\text{H}_2\text{O}$. **(a)** Illustration of Cu-sublattice. The rhombohedral unit cell contains 18 equivalent Cu atoms arranged in six chains with three atoms down the c -period. The inter/intra-chain magnetic couplings with strength J_2 and J_1 are indicated by white/black sticks. Left: an ab -plane. Not shown are the Si_6O_{18} rings, located inside the 12-membered Cu rings. The rhombus denotes the in-plane hexagonal unit cell. Right: two chiral chains along c . **(b)** Phase diagram of the magnetic sublattice as obtained by a Quantum Monte Carlo (QMC) simulation. At $\delta_c \approx 0.3$ a quantum phase transition occurs. The Néel temperature of

the antiferromagnetically ordered phase, for $\delta < \delta_c$, is given by the left axis. The antiferromagnetic order is of AB type with doubling of the unit cell along c . For $\delta > \delta_c$ a gap, given by the right axis, opens in the magnetic excitation spectrum and the state is a quantum spin liquid. **(c)** QMC results for the susceptibility for various δ values in comparison with the directional-averaged experimental susceptibility (solid line). Inset: the susceptibilities, χ , for magnetic fields parallel/orthogonal to the c -axis (lower/upper) curve. The vertical dashed lines indicate the location of T_N [02G1].

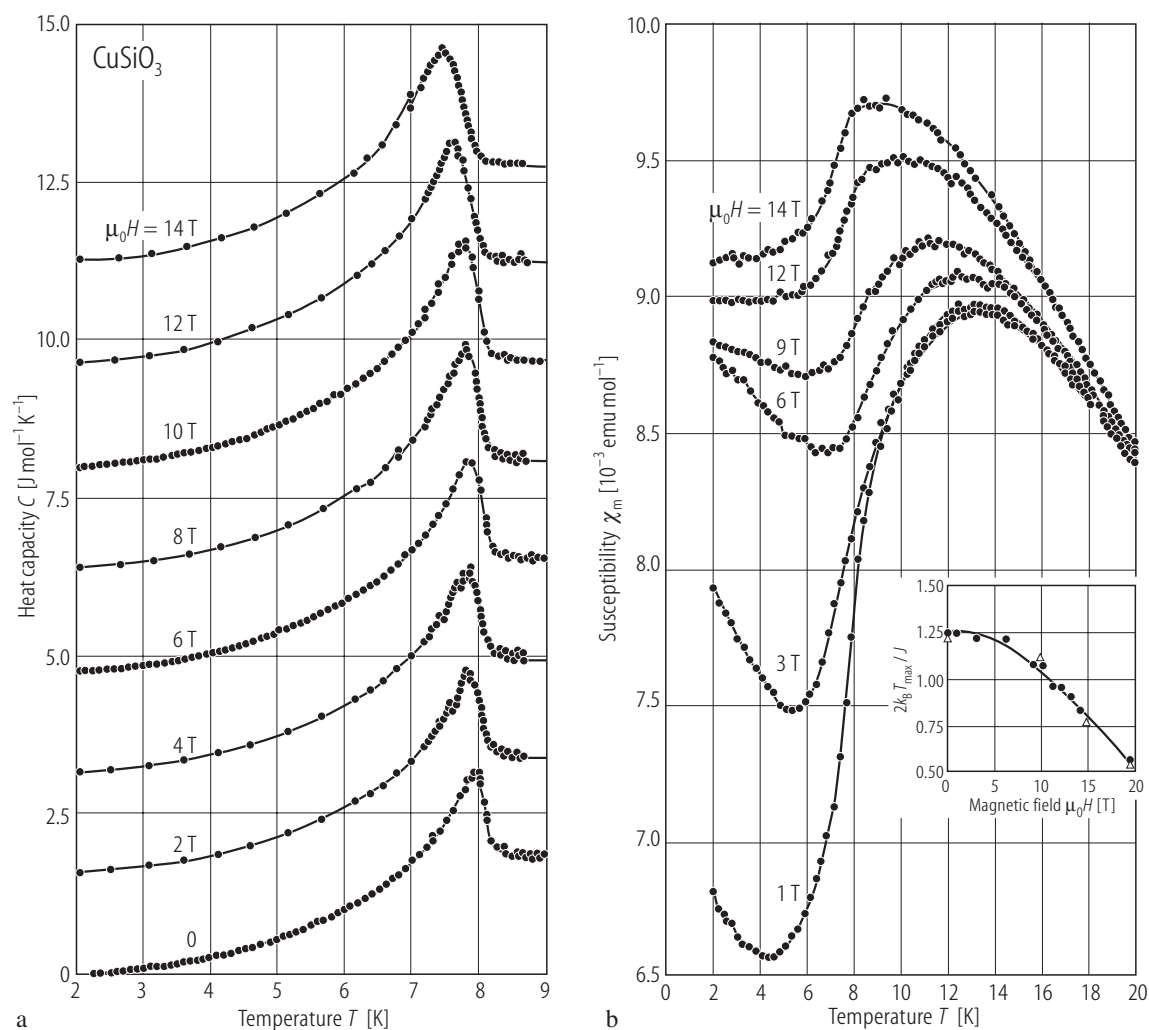


Fig. 12. CuSiO_3 . (a) Temperature dependence of the heat capacity. The origin of the vertical axis was shifted by 1.6 J/mol K for the curves with $\mu_0 H \geq 0$. In (b) the magnetic susceptibilities were plotted at various fields as function of temperature [00B1]. The inset shows the shift of the

temperature T_{max} , where the maxima in χ values were observed, in reduced units, as a function of applied field and in comparison with the theoretical prediction; triangles: [98K1]; circles: [00B1].

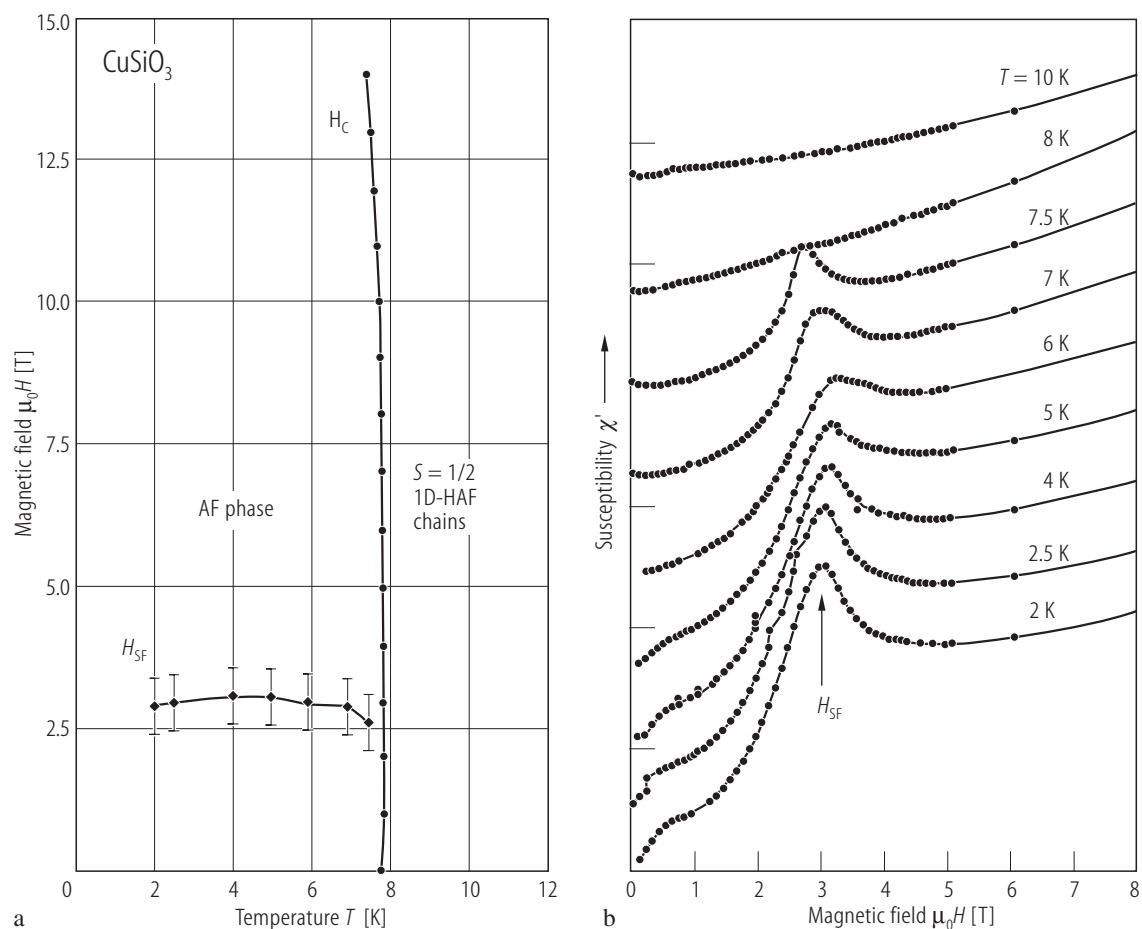


Fig. 13. CuSiO_3 . Magnetic phase diagram (a) obtained from heat capacity and susceptibility measurements. H_c denotes the field for the AF transition and H_{SF} the field for the spin-flop transition as evidenced from ac-susceptibility measurements (b). The origin of the vertical scale was shifted by a constant value for curves obtained at different temperatures [00B1].

For Fig. 14 see next page

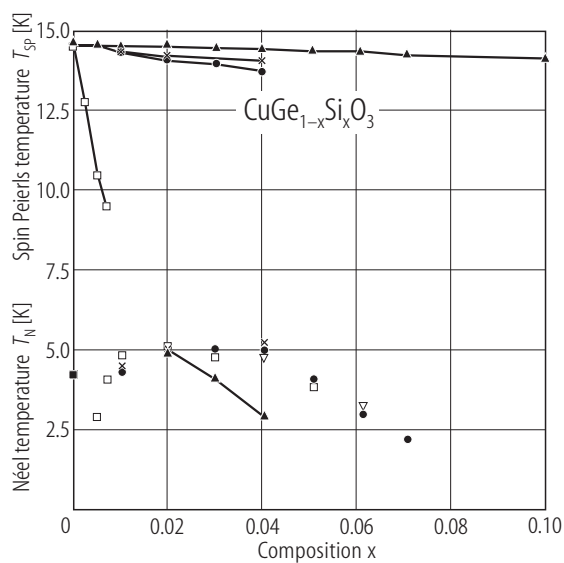


Fig. 15. $\text{CuGe}_{1-x}\text{Si}_x\text{O}_3$. Spin-Peierls (T_{SP}) and Néel (T_N) temperatures as function of composition for single crystals (sc) and reduced and unreduced polycrystals (pc) [97W1]. Open squares: sc from [95R1], open triangle: flux-grown sc, full triangles: unreduced pc, crosses: lightly reduced pc, full circles: highly reduced pc, full squares: $\text{CuGeO}_{2.9}$.

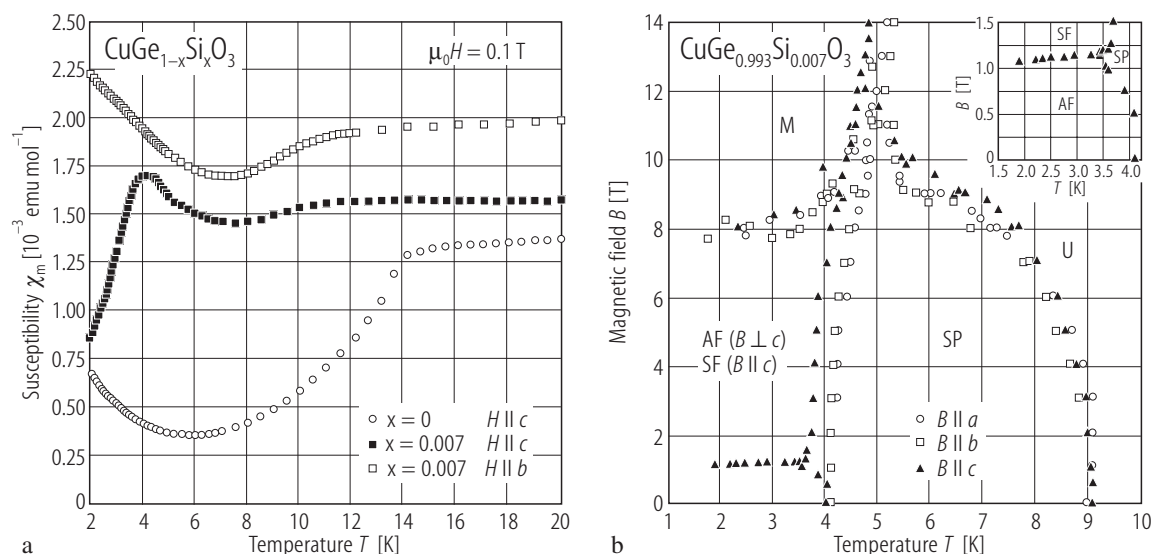


Fig. 14. $\text{CuGe}_{1-x}\text{Si}_x\text{O}_3$: **(a)** Magnetic susceptibilities as function of temperature for samples with $x = 0$ and 0.007 in a field of 0.1 T . **(b)** Magnetic phase diagram of a single crystal having $x = 0.007$ for magnetic fields oriented along the three orthorhombic axes. In inset, the bicritical point region is shown [95P1].

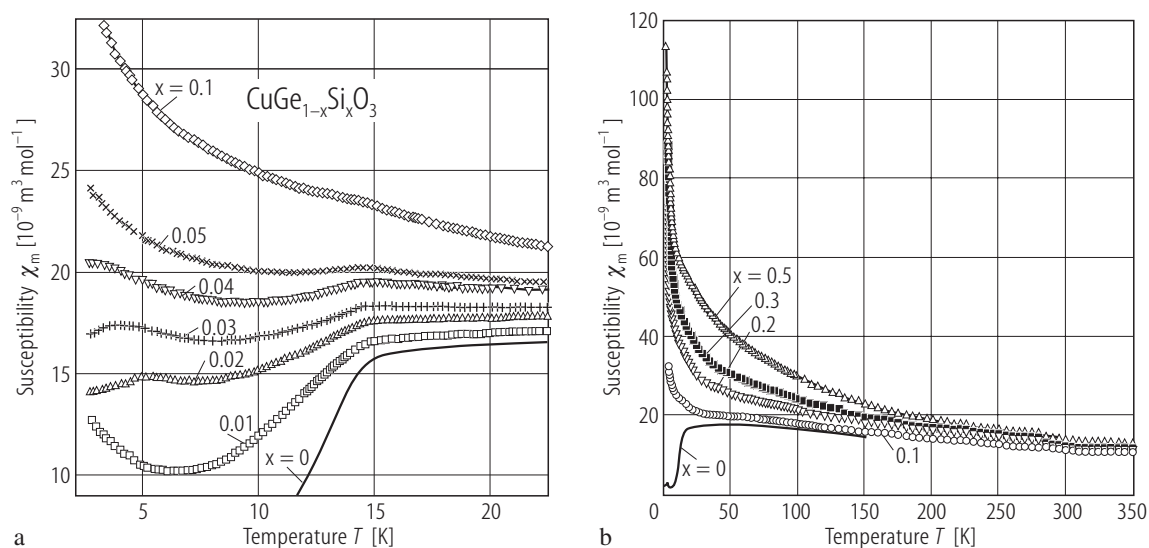


Fig. 16. $\text{CuGe}_{1-x}\text{Si}_x\text{O}_3$, polycrystalline samples. **(a)** Temperature dependences of the magnetic susceptibilities for $x \leq 0.1$. The spin-Peierls transition is seen up to $x = 0.1$. T_{SP} remains nearly unchanged. The Néel transition appears at $x = 0.02$ ($T_N = 5 \text{ K}$). T_N values decrease quite fast with increasing x down to 2.5 K for $4 \text{ at } \%$ Si. Both phase

transitions coexist for $0.02 \leq x \leq 0.04$ [97W1]. In **(b)** the temperature dependences of χ_m values for higher Si content than $x = 0.1$ are given [97W1]. With increasing Si content, the maximum at $\approx 56 \text{ K}$, characteristic of the one-dimensional behaviour, vanishes and is replaced by Curie-Weiss behaviour.

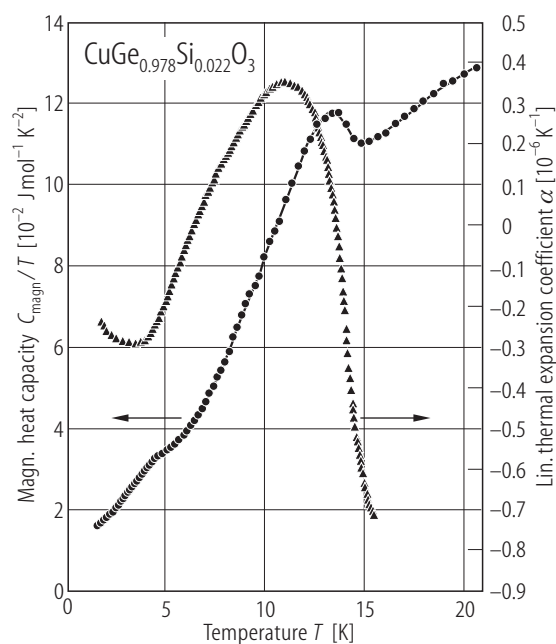


Fig. 17. $\text{CuGe}_{0.978}\text{Si}_{0.022}\text{O}_3$ polycrystal. Magnetic heat capacity (circles) and thermal expansion coefficient (triangles) as function of temperature [97W1].

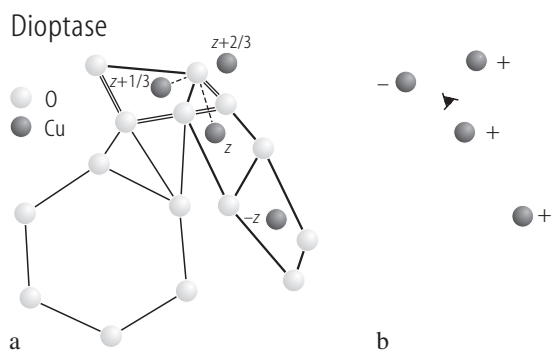


Fig. 18. Dioptase. The projection of a part of the unit cell of black dioptase onto the basal plane, showing the coordination of copper and the location of the silicate ring, $z_{\text{Cu}} = 0.0564$ (a); its magnetic structure (b) [93W1].

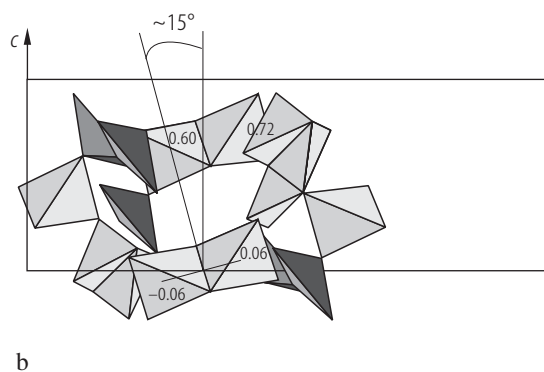
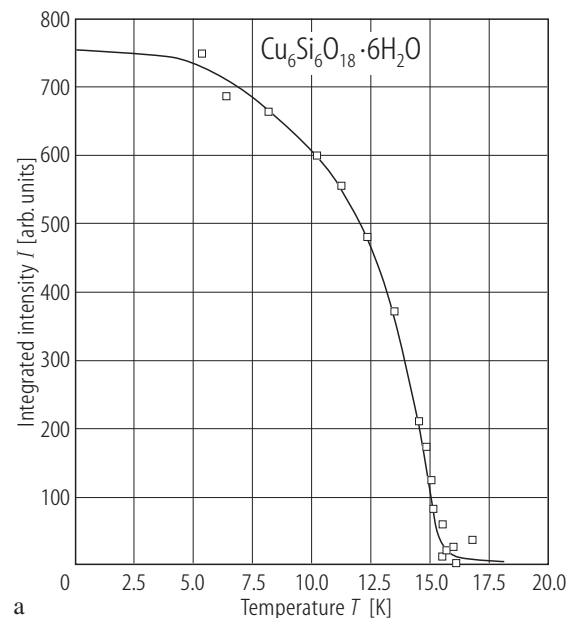


Fig. 19. Dioptase, $\text{Cu}_6\text{Si}_6\text{O}_{18} \cdot 6\text{H}_2\text{O}$. (a) Temperature dependence of the $(2,0,1/2)_{\text{hex}}$ reflection. (b) Fragment of the structure with triples of Cu squares at $z \approx 0$ and $z \approx 2/3$ along c_{hex} . The angle between the normal to the square and c_{hex} is shown [02B1].

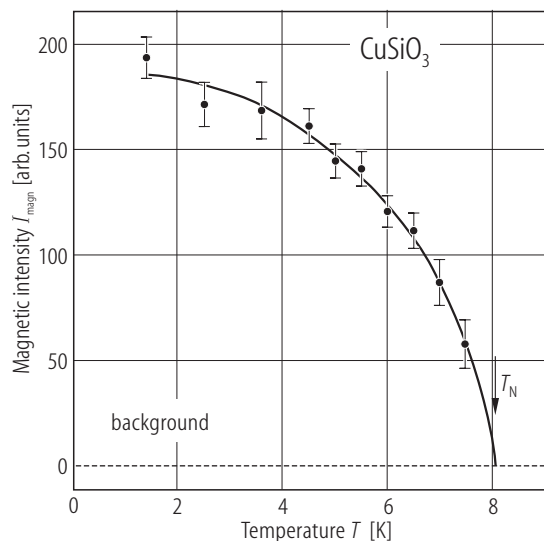


Fig. 20. CuSiO_3 . Temperature dependence of the integrated magnetic neutron diffraction intensities, I_{magn} , for the $(1/2, 1, -1/8)$ satellite [04W1].

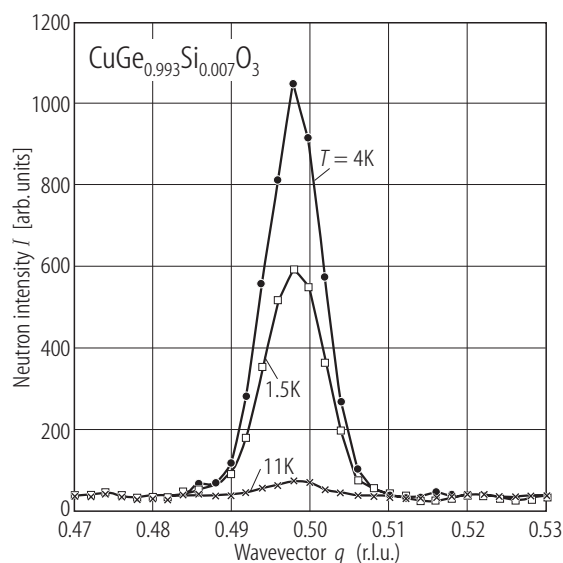


Fig. 21. $\text{CuGe}_{0.993}\text{Si}_{0.007}\text{O}_3$. Elastic neutron scattering scans around the dimerization peak $(1/2, 3, 1/2)$ at 1.5 K ($T \ll T_N$), 4 K ($T \approx T_N$) and 11 K ($T > T_{\text{Sp}}$). The persistence of the dimerization below the Néel temperature, T_N , of 3D-AF long-range order is observed [96R1].

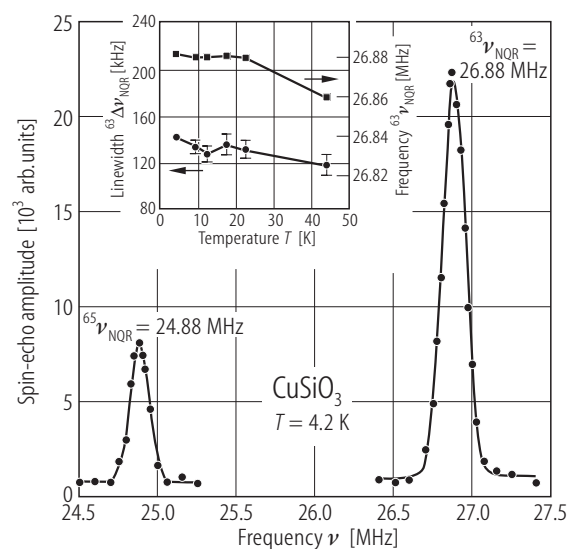


Fig. 22. CuSiO_3 . ^{63}Cu and ^{65}Cu NQR spectra at 4.2 K. The solid curves correspond to the fitting of a Gaussian function to the experimental data. The inset shows the temperature dependence of the ^{63}Cu NQR frequency (right axis) and of the ^{63}Cu NQR linewidths (left axis) [00B1].

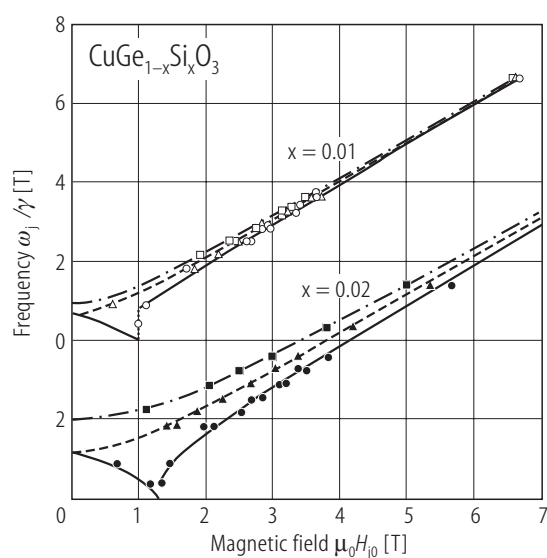


Fig. 23. $\text{CuGe}_{1-x}\text{Si}_x\text{O}_3$: AFMR frequency–field diagrams at 1.7 K for $x = 0.01$ and $x = 0.02$ samples [97N1]. Magnetic fields were applied along the *a* (open and full triangles), *b* (open and full squares) and *c* (open and full circles) axes, H_{j_0} ($j = a, b, c$) are the fields normalized by the *g* values, $H_{j_0} = g_j H/2$ ($j = a, b, c$).

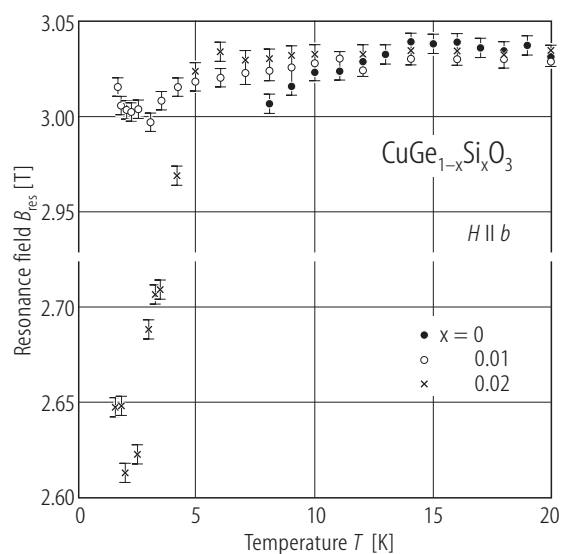


Fig. 24. $\text{CuGe}_{1-x}\text{Si}_x\text{O}_3$. Temperature dependences of the resonance field, B_{res} , at 95.5 GHz, for $x = 0, 0.01$ and 0.02 samples [97N1].

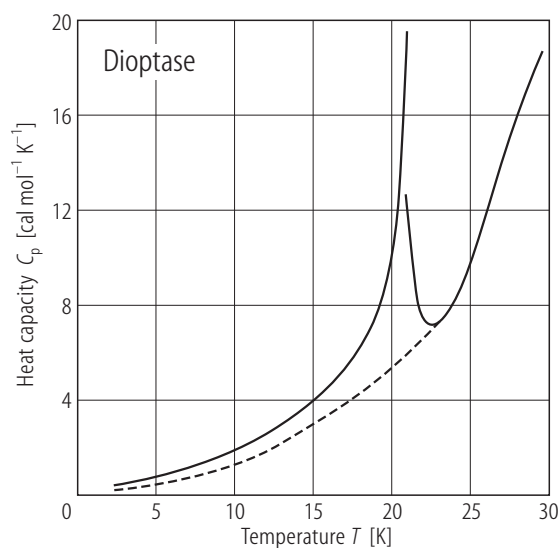


Fig. 25. Diopside, $\text{Cu}_6\text{Si}_6\text{O}_{18} \cdot 6\text{H}_2\text{O}$. Temperature dependence of heat capacity. The dashed line is the lattice contribution [64E1].

For Fig. 26 see next page

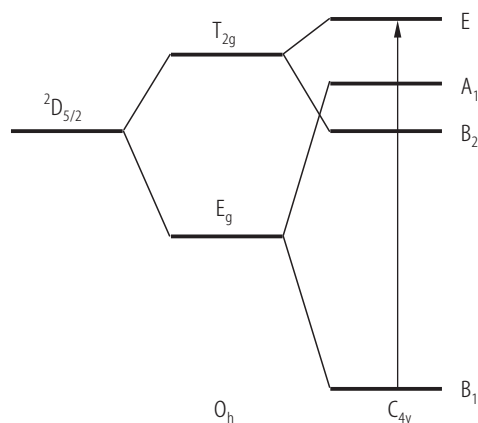
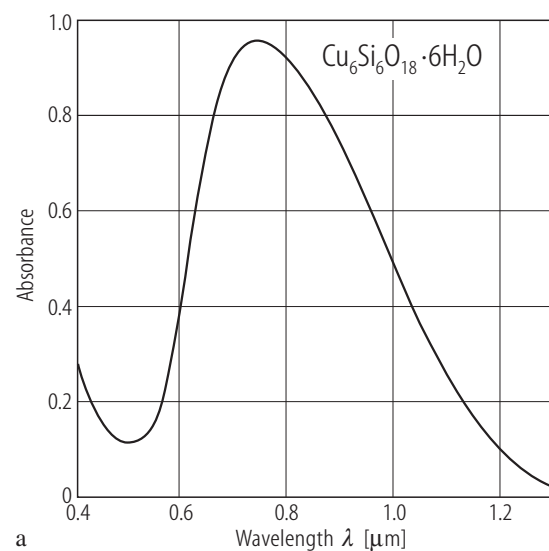


Fig. 27. Diopside, $\text{Cu}_6\text{Si}_6\text{O}_{18} \cdot 6\text{H}_2\text{O}$. **(a)** Diffuse reflectance spectrum. **(b)** Energy level diagram for a d^9 ion in an octahedral field modified by a square planar distortion with $c > a$ [67N1].

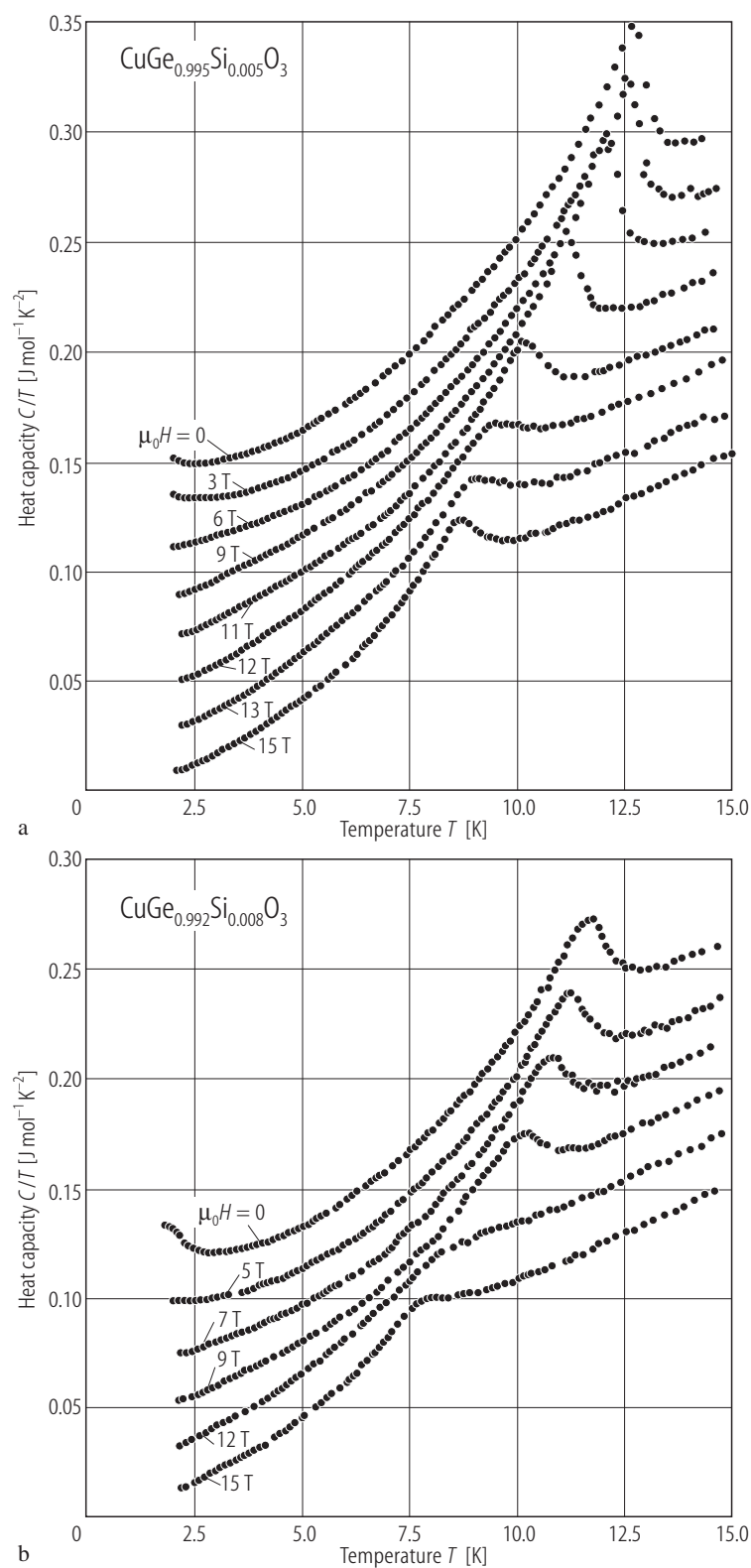


Fig. 26. $\text{CuGe}_{0.995}\text{Si}_{0.005}\text{O}_3$ (a), $\text{CuGe}_{0.992}\text{Si}_{0.008}\text{O}_3$ (b). Temperature dependences of the heat capacities under a magnetic field parallel to the a -axis in the form C/T vs T . The origin of vertical axis is shifted by 0.02 J/mol K^2 [98H2].

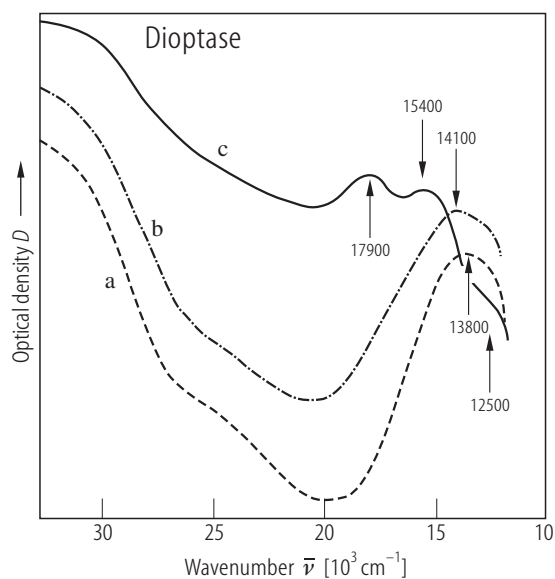


Fig. 28. Green (a), blue (b) and black (c) diopside. Ligand field spectra (UV) [88B1].

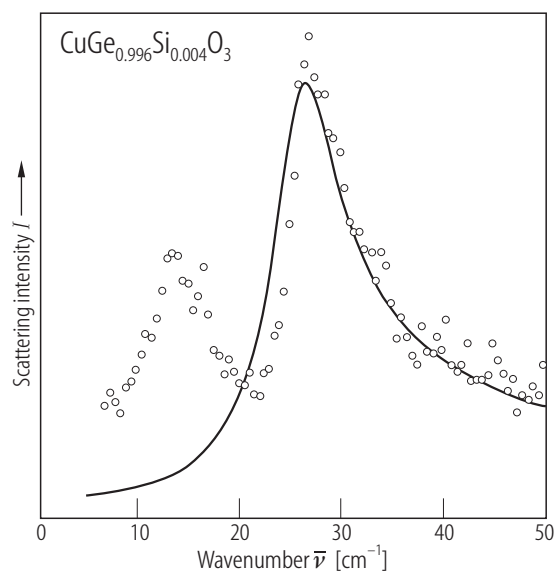


Fig. 32. $\text{CuGe}_{0.996}\text{Si}_{0.004}\text{O}_3$. Raman spectrum at 3 K. Solid curves denote the theory [98S1].

For Figs. 29, 31 see next pages

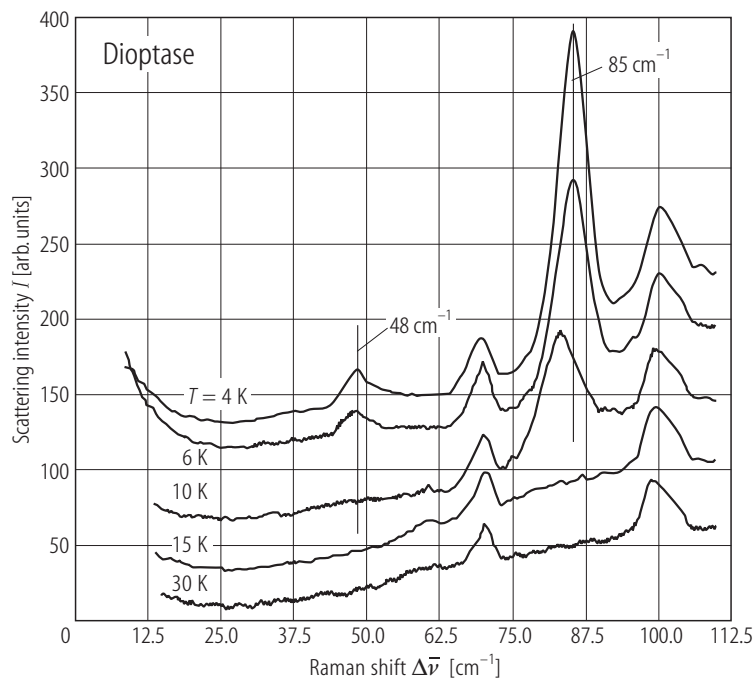


Fig. 30. Diopside, $\text{Cu}_6\text{Si}_6\text{O}_{18}\cdot 6\text{H}_2\text{O}$. Low-energy Raman spectrum of green diopside in XX polarization. The modes at 48 and 85 cm^{-1} ($\cong 69$ and 122 K) show a strong increase of intensity at $T < T_N$ and correspond to one- and two-magnon processes. The temperature-independent modes at 70 and 100 cm^{-1} are phonons [02G1].

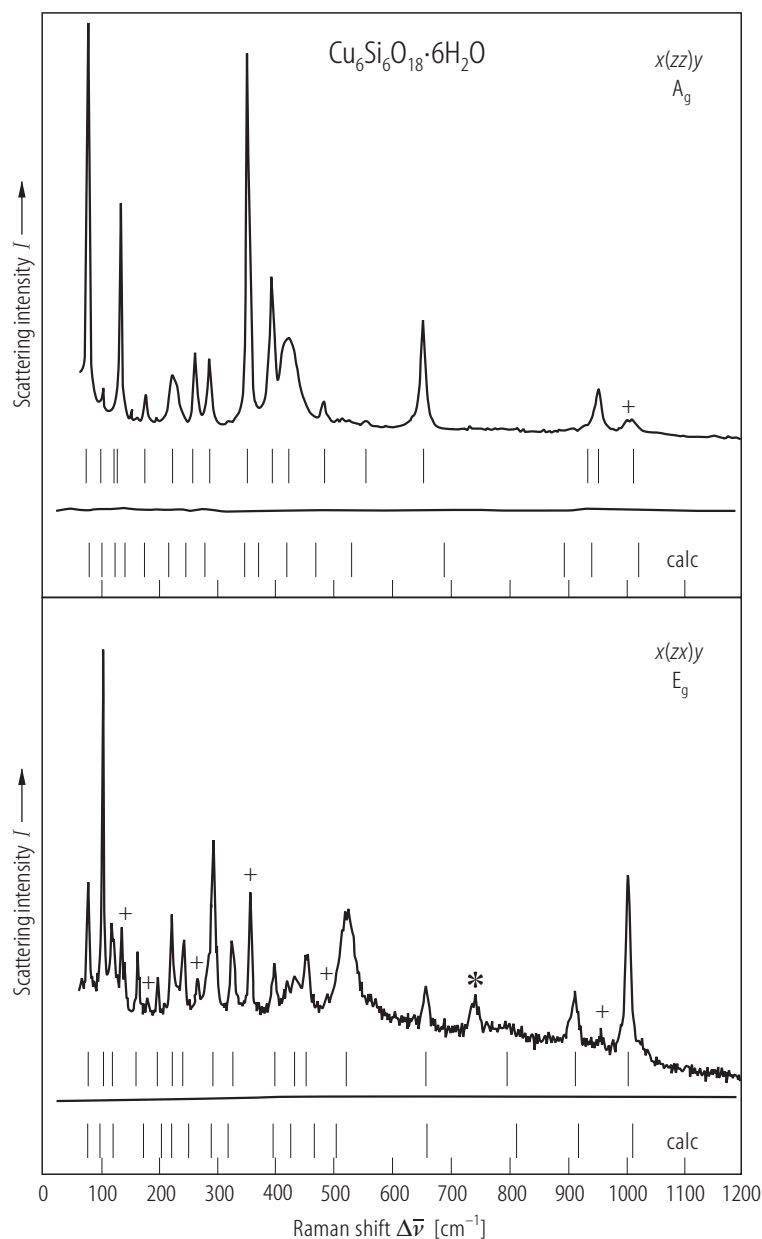


Fig. 29. Diopside, $\text{Cu}_6\text{Si}_6\text{O}_{18} \cdot 6\text{H}_2\text{O}$. Raman spectra of A_g and E_g symmetries. Below, fundamental frequencies are indicated as vertical bars. By* is indicated a combination or overtone, and + indicates leakage from the other symmetry species. Labeled as calculated (calc), are the frequencies from the normal coordinate analysis plotted as vertical bars [95M1].

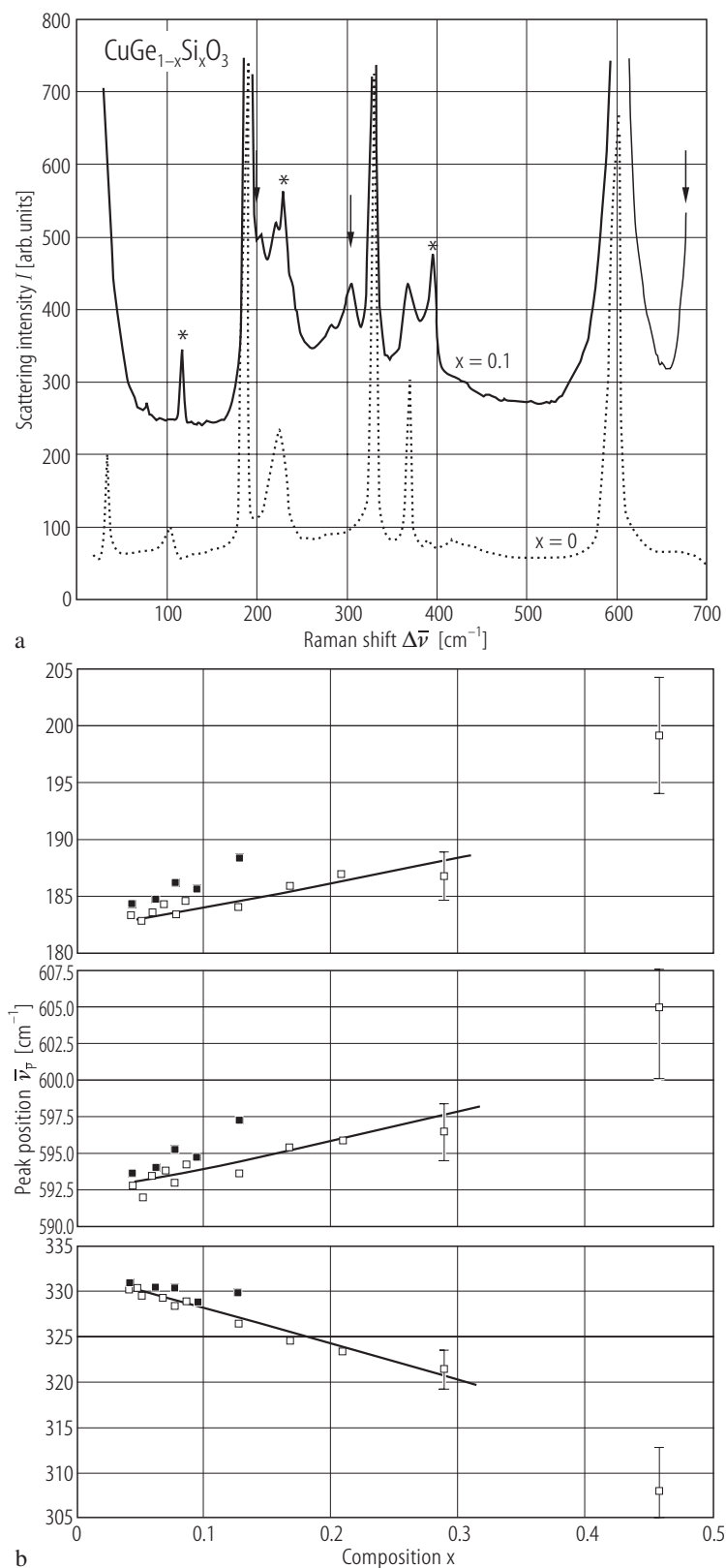


Fig. 31. $\text{CuGe}_{1-x}\text{Si}_x\text{O}_3$. **(a)** Normalized Raman-scattering intensity for compositions $x = 0$ and 0.1 . The asterisks mark symmetry-forbidden phonon modes and the arrows defect modes induced by the substitution. **(b)** Some optical-phonon frequencies at room temperature vs composition. Linear composition dependences was shown up to $x = 0.3$. The other phonon frequencies which were not shown, remain unchanged. Solid symbols refer to sc's, open ones to pc samples. The sample with $x = 0.5$ shows a significant larger change of phonon frequency [97W1].